

10EDA60

PRV : 600 Volts
Io : 1.0 Ampere

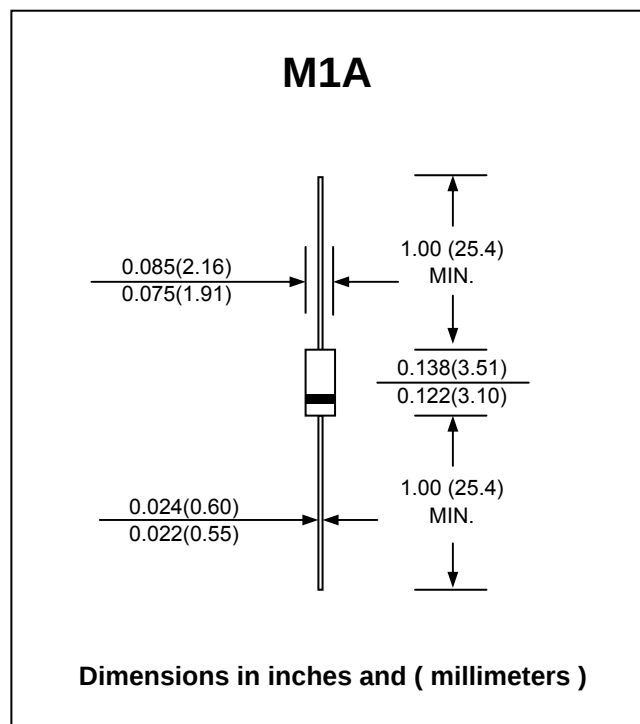
FEATURES :

- * Glass passivated junction chip
- * High Surge Capability
- * Low Forward Voltage drop
- * Low Reverse Leakage Current
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : M1A Molded plastic
- * Epoxy : UL94V-O rate flame retardant
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.20 gram (approximately)

SILICON RECTIFIER DIODE



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	600	V
Maximum Average Forward Current Ta = 39 °C 50 Hz Half Sine wave Resistive Load Ta = 26 °C	$I_{F(AV)}$	1.0 ⁽¹⁾ 0.9 ⁽²⁾	A
Maximum Surge Forward Current, Non-repetitive 50Hz Half Sine Wave, 1cycle	I_{FSM}	45	A
Maximum Peak Forward Voltage, Tj = 25 °C, $I_{FM} = 1.0A$	V_{FM}	1.0	V
Maximum Peak Reverse Current, Tj = 25 °C, $V_{RM} = V_{RRM}$	I_{RM}	10	μA
Maximum Thermal Resistance Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	110	°C/W
Operating Junction Temperature Range	T_J	- 40 to + 150	°C
Storage Temperature Range	T_{STG}	- 40 to + 150	°C

Notes :

- (1) P.C. Board mounted (L = 3 mm, Print Land = 5 × 5 mm, Both Sides)
(2) Without Fin or P.C. Board mounted.

RATING AND CHARACTERISTIC CURVES (10EDA60)

FIG.1 - AVERAGE FORWARD CURRENT VS. AMBIENT TEMPERATURE

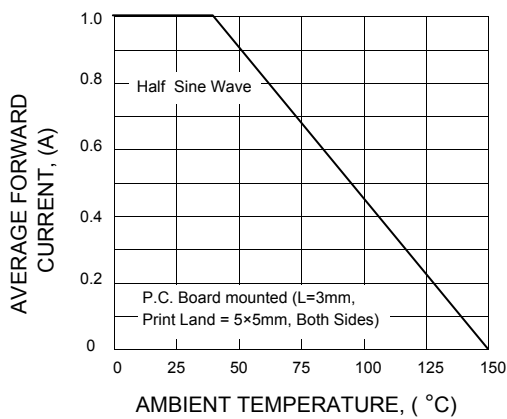


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

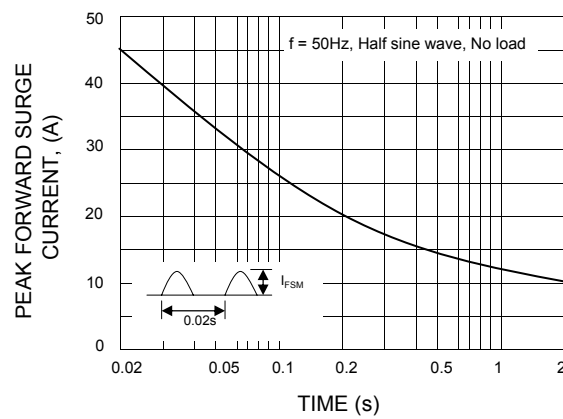


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

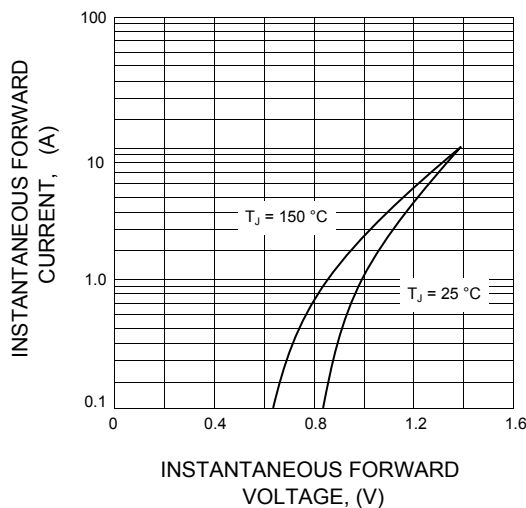


FIG.4 - AVERAGE FORWARD POWER DISSIPATION

